

VOLTAGE RANGE: 200V
CURRENT: 500mA

Features

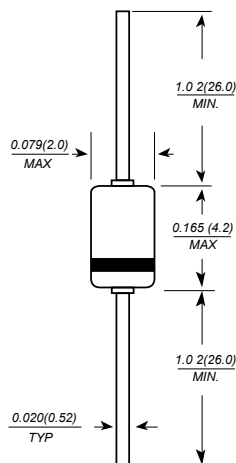
- Silicon Epitaxial Planar Diodes
- Micro Melf package

Mechanical Data

- Case : DO-35 Glass Case
- Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- Polarity : Color band denotes cathode end
- Mounting position : Any
- Weight : 0.13 gram (approximately)



DO-35(GLASS)



Dimensions in millimeters

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{RRM}	Maximum Repetitive Reverse Voltage	200	V
$I_{F(AV)}$	Average Rectified Forward Current	500	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0	A
		4.0	A
T_{STG}	Storage Temperature Range	-65 to +200	$^\circ\text{C}$
T	Operating Junction Temperature	175	$^\circ\text{C}$
Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	$^\circ\text{C}$

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Max.	Units
V_R	Breakdown Voltage	$I_R = 100\mu\text{A}$	200		V
V_F	Forward Voltage	$I_F = 100\text{mA}$		1.0	V
I_R	Reverse Leakage	$V_R = 175\text{V}$		100	nA
		$V_R = 175\text{V}, T_A = 150^\circ\text{C}$		100	μA
C_T	Total Capacitance	$V_R = 0\text{V}, f = 1.0\text{MHz}$		5	pF
t_{rr}	Reverse Recovery Time	$I_F = I_R = 30\text{mA}, R_L = 100\Omega$		50	ns